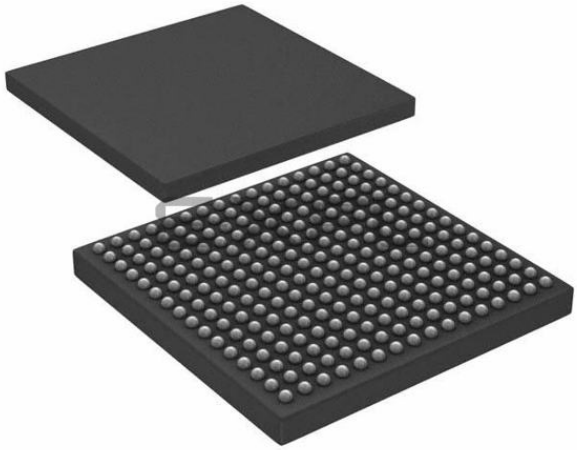

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z2, e200z4
Core Size	32-Bit Dual-Core
Speed	80MHz, 160MHz
Connectivity	CANbus, Ethernet, FlexRay, I²C, LINbus, SPI
Peripherals	DMA, I²S, POR, WDT
Number of I/O	178
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	3.15V ~ 5.5V
Data Converters	A/D 36x10b, 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	256-LBGA
Supplier Device Package	256-MAPPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5745cbk1ammj6

NOTE

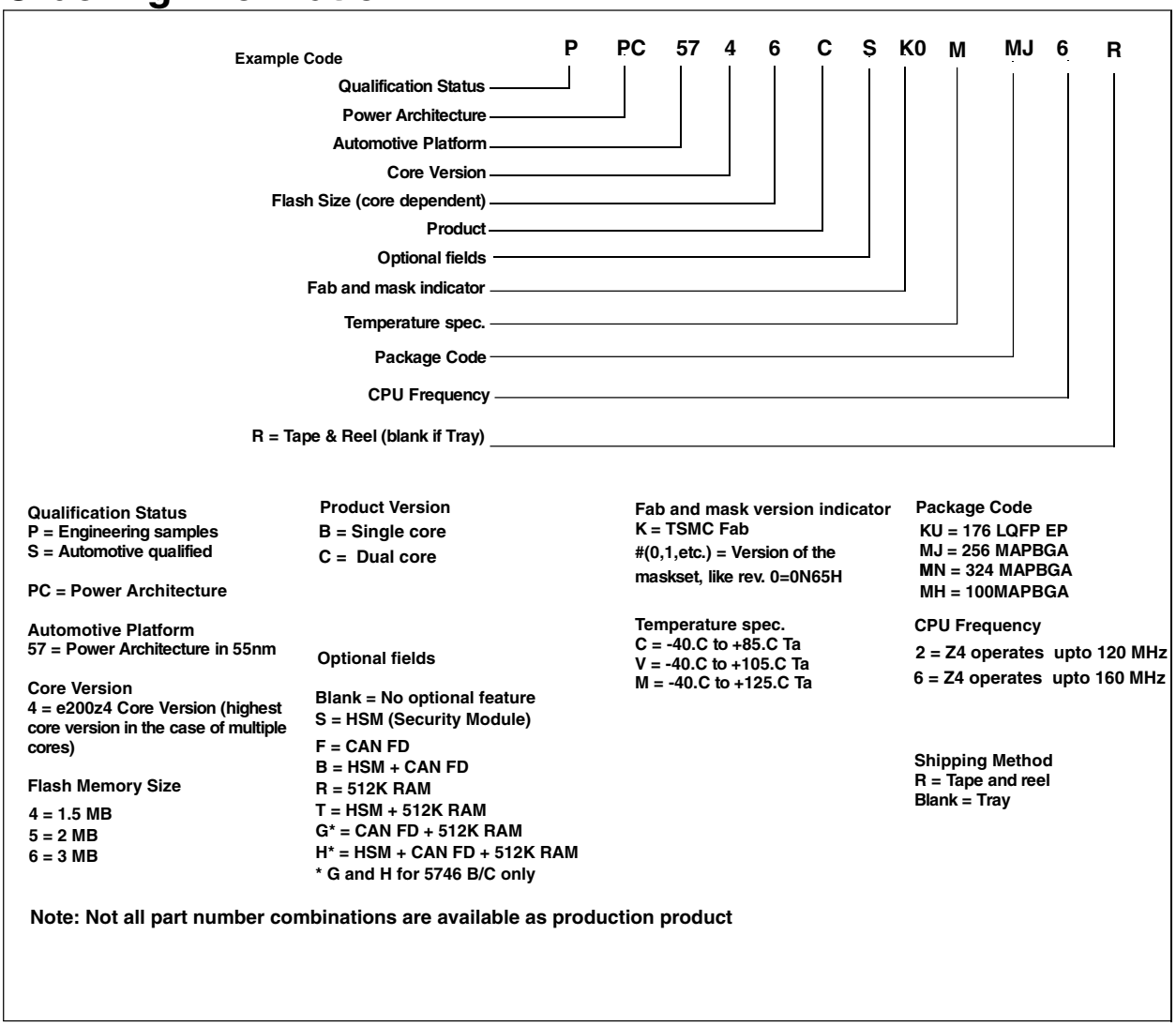
All optional features (Flash memory, RAM, Peripherals) start with lowest number or address (e.g., FlexCAN0) and end at highest available number or address (e.g., MPC574xB/C have 6 CAN, ending with FlexCAN5).

Table 1. MPC5746C Family Comparison[1]

Feature	MPC5745B	MPC5744B	MPC5746B	MPC5744C	MPC5745C	MPC5746C
CPUs	e200z4	e200z4	e200z4	e200z4 e200z2	e200z4 e200z2	e200z4 e200z2
FPU	e200z4	e200z4	e200z4	e200z4	e200z4	e200z4
Maximum Operating Frequency[2]	160MHz (Z4)	160MHz (Z4)	160MHz (Z4)	160MHz (Z4) 80MHz (Z2)	160MHz (Z4) 80MHz (Z2)	160MHz (Z4) 80MHz (Z2)
Flash memory	2 MB	1.5 MB	3 MB	1.5 MB	2 MB	3 MB
EEPROM support	Emulated up to 64K			Emulated up to 64K		
RAM	256 KB	192 KB	384 KB (Optional 512KB)[3, 3]	192 KB	256 KB	384 KB (Optional 512KB)[3]
ECC	End to End					
SMPU	16 entry					
DMA	32 channels					
10-bit ADC	36 Standard channels 32 External channels					
12-bit ADC	15 Precision channels 16 Standard channels					
Analog Comparator	3					
BCTU	1					
SWT	1, SWT[0][4]			2[4]		
STM	1, STM[0]			2		
PIT-RTI	16 channels PIT 1 channels RTI					
RTC/API	1					
Total Timer I/O[5]	64 channels 16-bits					
LINFlexD	1 Master and Slave (LINFlexD[0], 11 Master (LINFlexD[1:11])			1 Master and Slave (LINFlexD[0], 15 Master (LINFlexD[1:15])		
FlexCAN	6 with optional CAN FD support (FlexCAN[0:5])			8 with optional CAN FD support (FlexCAN[0:7])		
DSPI/SPI	4 x DSPI 4 x SPI					

Table continues on the next page...

3.2 Ordering Information



Note: Not all part number combinations are available as production product

4 General

4.1 Absolute maximum ratings

NOTE

Functional operating conditions appear in the DC electrical characteristics. Absolute maximum ratings are stress ratings only, and functional operation at the maximum values is not guaranteed. See footnotes in Table 5 for specific conditions

4. VDD_LV supply pins should never be grounded (through a small impedance). If these are not driven, they should only be left floating
5. VIN1_CMP_REF ≤ VDD_HV_A
6. This supply is shorted VDD_HV_A on lower packages.
7. T_J=150°C. Assumes T_A=125°C
    - Assumes maximum θJA of 2s2p board. See Thermal attributes

4.3 Voltage regulator electrical characteristics

The voltage regulator is composed of the following blocks:

- Choice of generating supply voltage for the core area.
    - Control of external NPN ballast transistor
    - Generating core supply using internal ballast transistor
    - Connecting an external 1.25 V (nominal) supply directly without the NPN ballast
- Internal generation of the 3.3 V flash supply when device connected in 5V applications
- External bypass of the 3.3 V flash regulator when device connected in 3.3V applications
- Low voltage detector - low threshold (LVD_IO_A_LO) for $V_{DD\_HV\_IO\_A\ supply}$
- Low voltage detector - high threshold (LVD_IO_A_Hi) for $V_{DD\_HV\_IO\_A\ supply}$
- Low voltage detector (LVD_FLASH) for 3.3 V flash supply (VDD_HV_FLA)
- Various low voltage detectors (LVD_LV_x)
- High voltage detector (HVD_LV_cold) for 1.2 V digital core supply (VDD_LV)
- Power on Reset (POR_LV) for 1.25 V digital core supply (VDD_LV)
- Power on Reset (POR_HV) for 3.3 V to 5 V supply (VDD_HV_A)

The following bipolar transistors[1] are supported, depending on the device performance requirements. As a minimum the following must be considered when determining the most appropriate solution to maintain the device under its maximum power dissipation capability: current, ambient temperature, mounting pad area, duty cycle and frequency for Idd, collector voltage, etc

1. BCP56, MCP68 and MJD31are guaranteed ballasts.

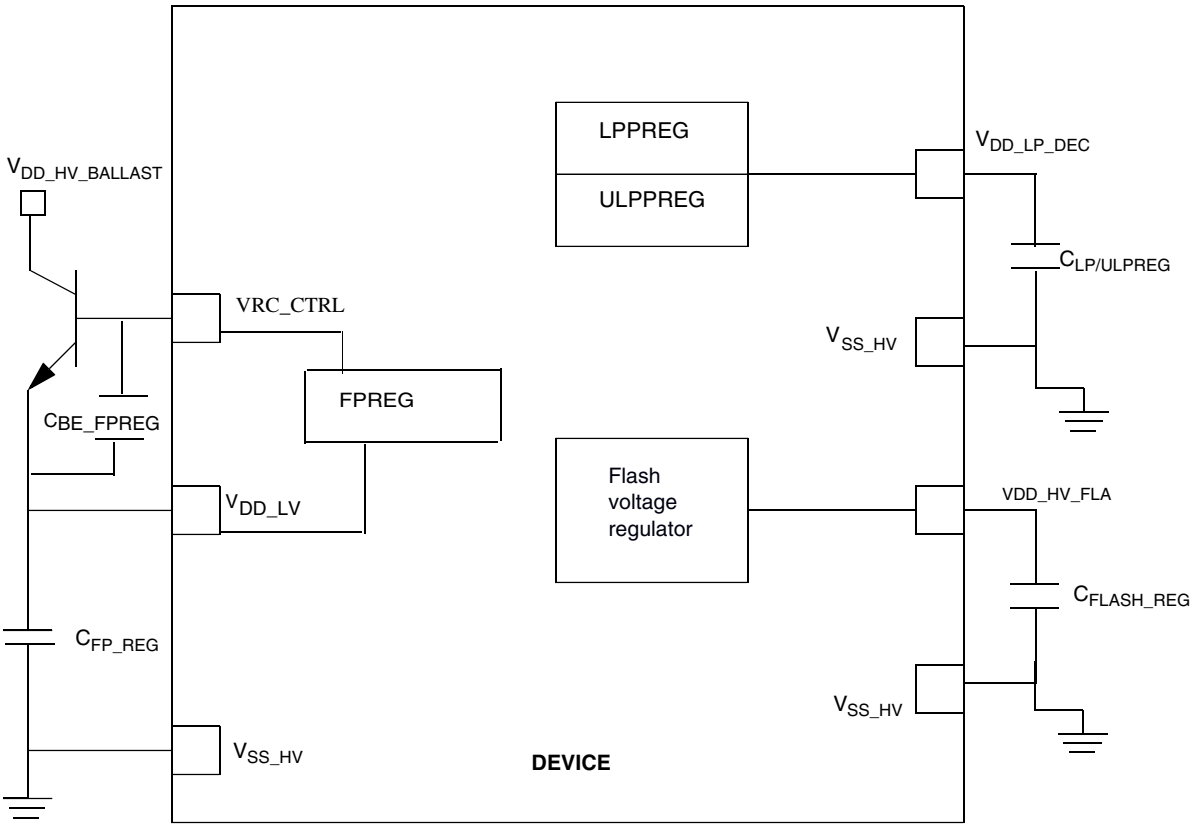


Figure 2. Voltage regulator capacitance connection

NOTE

On BGA, VSS_LV and VSS_HV have been joined on substrate and renamed as VSS.

Table 8. Voltage regulator electrical specifications

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{fp_reg}[1]	External decoupling / stability capacitor	Min, max values shall be granted with respect to tolerance, voltage, temperature, and aging variations.	1.32	2.2[2]	3	µF
	Combined ESR of external capacitor	—	0.001	—	0.03	Ohm
C_{lp/ulp_reg}	External decoupling / stability capacitor for internal low power regulators	Min, max values shall be granted with respect to tolerance, voltage, temperature, and aging variations.	0.8	1	1.4	µF
	Combined ESR of external capacitor	—	0.001	—	0.1	Ohm
C_{be_fpreg}[3]	Capacitor in parallel to base-emitter	BCP68 and BCP56		3.3		nF
		MJD31		4.7		

Table continues on the next page...

Table 9. Voltage monitor electrical characteristics (continued)

Symbol	Parameter	State	Conditions	Configuration			Threshold			Unit
				Power Up [1]	Mask Opt[2, 2]	Reset Type	Min	Typ	Max	V
$V_{LVD\_LV\_PD2\_cold}$	LV supply low voltage monitoring, detecting at the device pin	Fall	Untrimmed	No	Yes	Functional	Disabled at Start			
			Trimmed				1.1400	1.1550	1.1750	V
		Rise	Untrimmed				Disabled at Start			
			Trimmed				1.1600	1.1750	1.1950	V

1. All monitors that are active at power-up will gate the power up recovery and prevent exit from POWERUP phase until the minimum level is crossed. These monitors can in some cases be masked during normal device operation, but when active will always generate a destructive reset.
2. Voltage monitors marked as non maskable are essential for device operation and hence cannot be masked.
3. There is no voltage monitoring on the $V_{DD\_HV\_ADC0}$, $V_{DD\_HV\_ADC1}$, $V_{DD\_HV\_B}$ and $V_{DD\_HV\_C}$ I/O segments. For applications requiring monitoring of these segments, either connect these to $V_{DD\_HV\_A}$ at the PCB level or monitor externally.

4.5 Supply current characteristics

Current consumption data is given in the following table. These specifications are design targets and are subject to change per device characterization.

NOTE

The ballast must be chosen in accordance with the ballast transistor supplier operating conditions and recommendations.

Table 10. Current consumption characteristics

Symbol	Parameter	Conditions[1]	Min	Typ	Max	Unit
$I_{DD\_BODY\_1}$ [2, 3]	RUN Body Mode Profile Operating current	LV supply + HV supply + HV Flash supply + 2 x HV ADC supplies[4, 4] T_a = 125°C [5, 5] V_{DD_LV} = 1.25 V VDD_HV_A = 5.5V SYS_CLK = 80MHz	—	—	147	mA
		T_a = 105°C	—	—	142	mA
		T_a = 85 °C	—	—	137	mA

Table continues on the next page...

Table 10. Current consumption characteristics (continued)

Symbol	Parameter	Conditions[1]	Min	Typ	Max	Unit
$I_{DD\_BODY\_2}$ 6	RUN Body Mode Profile Operating current	LV supply + HV supply + HV Flash supply + 2 x HV ADC supplies[4] T_a = 125°C[5] V_{DD_LV} = 1.25 V VDD_HV_A = 5.5V SYS_CLK = 160MHz	—	—	246	mA
		T_a = 105°C	—	—	235	mA
		T_a = 85°C	—	—	210	mA
$I_{DD\_BODY\_3}$ 7	RUN Body Mode Profile Operating current	LV supply + HV supply + HV Flash supply + 2 x HV ADC supplies[4] T_a = 125 °C [5] V_{DD_LV} = 1.25 V VDD_HV_A = 5.5V SYS_CLK = 120MHz	—	—	181	mA
		T_a = 105 °C	—	—	176	mA
		T_a = 85°C	—	—	171	mA
$I_{DD\_BODY\_4}$[8]	RUN Body Mode Profile Operating current	LV supply + HV supply + HV Flash supply + 2 x HV ADC supplies[4] T_a = 125 °C [5] V_{DD_LV} = 1.25 V VDD_HV_A = 5.5V SYS_CLK = 120MHz	—	—	264	mA
		T_a = 105 °C	—	—	176	mA
		T_a = 85 °C	—	—	171	mA
I_{DD_STOP}	STOP mode Operating current	T_a = 125 °C[9] V_{DD_LV} = 1.25 V	—	—	49	mA
		T_a = 105 °C V_{DD_LV} = 1.25 V	—	10.6	—	
		T_a = 85 °C V_{DD_LV} = 1.25 V	—	8.1	—	
		T_a = 25 °C V_{DD_LV} = 1.25 V	—	4.6	—	

Table continues on the next page...

Table 12. STANDBY Current consumption characteristics (continued)

Symbol	Parameter	Conditions[1]	Min	Typ	Max	Unit
STANDBY2	STANDBY with 128K RAM	T_a = 25 °C	—	75	—	µA
		T_a = 85 °C	—	155	730	
		T_a = 105 °C	—	255	1350	
		T_a = 125 °C [2]	—	396	2600	
STANDBY3	STANDBY with 256K RAM	T_a = 25 °C	—	80	—	µA
		T_a = 85 °C	—	180	800	
		T_a = 105 °C	—	290	1425	
		T_a = 125 °C [2]	—	465	2900	
STANDBY3	FIRC ON	T_a = 25 °C	—	500	—	µA

1. The content of the Conditions column identifies the components that draw the specific current.
2. Assuming Ta=Tj, as the device is in static (fully clock gated) mode. Assumes maximum θJA of 2s2p board. SeeThermal attributes

4.6 Electrostatic discharge (ESD) characteristics

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n + 1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard.

NOTE

A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 13. ESD ratings

Symbol	Parameter	Conditions[1]	Class	Max value[2]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500 750 (corners)	V

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. Data based on characterization results, not tested in production.

Table 18. Functional reset pad electrical specifications (continued)

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
V_{HYS}	CMOS Input Buffer hysterisis	—	300	—	—	mV
V_{DD_POR}	Minimum supply for strong pull-down activation	—	—	—	1.2	V
I_{OL_R}	Strong pull-down current [1, 1]	Device under power-on reset $V_{DD\_HV\_A}$= V_{DD_POR} V_{OL} = 0.35*$V_{DD\_HV\_A}$	0.2	—	—	mA
		Device under power-on reset $V_{DD\_HV\_A}$= V_{DD_POR} V_{OL} = 0.35*$V_{DD\_HV\_IO}$	11	—	—	mA
W_{FRST}	$\overline{\text{RESET}}$ input filtered pulse	—	—	—	500	ns
W_{NFRST}	$\overline{\text{RESET}}$ input not filtered pulse	—	2000	—	—	ns
$\|I_{WPU}\|$	Weak pull-up current absolute value	RESET pin V_{IN} = V_{DD}	23	—	82	µA

1. Strong pull-down is active on PHASE0, PHASE1, PHASE2, and the beginning of PHASE3 for RESET.

5.6 PORST electrical specifications

Table 19. PORST electrical specifications

Symbol	Parameter	Value			Unit
		Min	Typ	Max	
W_{FPORST}	$\overline{\text{PORST}}$ input filtered pulse	—	—	200	ns
$W_{NFPORST}$	$\overline{\text{PORST}}$ input not filtered pulse	1000	—	—	ns
V_{IH}	Input high level	0.65 x $V_{DD\_HV\_A}$	—	—	V
V_{IL}	Input low level	—	—	0.35 x $V_{DD\_HV\_A}$	V

6 Peripheral operating requirements and behaviours

6.1 Analog

6.1.1 ADC electrical specifications

The device provides a 12-bit Successive Approximation Register (SAR) Analog-to-Digital Converter.

6.1.2 Analog Comparator (CMP) electrical specifications

Table 22. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	250	µA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	5	11	µA
V_{AIN}	Analog input voltage	V_{SS}	—	$V_{IN1\_CMP\_REF}$	V
V_{AIO}	Analog input offset voltage [1, 1]	-47	—	47	mV
V_H	Analog comparator hysteresis [2, 2]	—	1	25	mV
	• CR0[HYSTCTR] = 00	—	20	50	mV
	• CR0[HYSTCTR] = 01	—	40	70	mV
	• CR0[HYSTCTR] = 10	—	60	105	mV
	• CR0[HYSTCTR] = 11				
t_{DHS}	Propagation Delay, High Speed Mode (Full Swing) [1, 3, 3]	—	—	250	ns
t_{DLS}	Propagation Delay, Low power Mode (Full Swing) [1, 3]	—	5	21	µs
	Analog comparator initialization delay, High speed mode[4, 4]	—	4		µs
	Analog comparator initialization delay, Low speed mode [4]	—	100		µs
I_{DAC6b}	6-bit DAC current adder (when enabled)				
	3.3V Reference Voltage	—	6	9	µA
	5V Reference Voltage	—	10	16	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[5]
DNL	6-bit DAC differential non-linearity	–0.8	—	0.8	LSB

1. Measured with hysteresis mode of 00
2. Typical hysteresis is measured with input voltage range limited to 0.6 to $V_{DD\_HV\_A}$-0.6V
3. Full swing = VIH, VIL
4. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
5. 1 LSB = $V_{reference}/64$

Table 30. Flash memory program and erase specifications

Symbol	Characteristic[1]	Typ[2]	Factory Programming[3, 4]		Field Update			Unit
			Initial Max	Initial Max, Full Temp	Typical End of Life[5]	Lifetime Max[6]		
			20°C ≤T_A ≤30°C	-40°C ≤T_J ≤150°C	-40°C ≤T_J ≤150°C	≤ 1,000 cycles	≤ 250,000 cycles	
t_{dwpgm}	Doubleword (64 bits) program time	43	100	150	55	500		µs
t_{ppgm}	Page (256 bits) program time	73	200	300	108	500		µs
t_{qppgm}	Quad-page (1024 bits) program time	268	800	1,200	396	2,000		µs
t_{16kers}	16 KB Block erase time	168	290	320	250	1,000		ms
t_{16kpgm}	16 KB Block program time	34	45	50	40	1,000		ms
t_{32kers}	32 KB Block erase time	217	360	390	310	1,200		ms
t_{32kpgm}	32 KB Block program time	69	100	110	90	1,200		ms
t_{64kers}	64 KB Block erase time	315	490	590	420	1,600		ms
t_{64kpgm}	64 KB Block program time	138	180	210	170	1,600		ms
$t_{256kers}$	256 KB Block erase time	884	1,520	2,030	1,080	4,000	—	ms
$t_{256kpgm}$	256 KB Block program time	552	720	880	650	4,000	—	ms

1. Program times are actual hardware programming times and do not include software overhead. Block program times assume quad-page programming.
2. Typical program and erase times represent the median performance and assume nominal supply values and operation at 25 °C. Typical program and erase times may be used for throughput calculations.
3. Conditions: ≤ 150 cycles, nominal voltage.
4. Plant Programing times provide guidance for timeout limits used in the factory.
5. Typical End of Life program and erase times represent the median performance and assume nominal supply values. Typical End of Life program and erase values may be used for throughput calculations.
6. Conditions: -40°C ≤ T_J ≤ 150°C, full spec voltage.

6.3.2 Flash memory Array Integrity and Margin Read specifications

Table 31. Flash memory Array Integrity and Margin Read specifications

Symbol	Characteristic	Min	Typical	Max[1, 1]	Units[2, 2]
$t_{ai16kseq}$	Array Integrity time for sequential sequence on 16 KB block.	—	—	512 x Tperiod x Nread	—
$t_{ai32kseq}$	Array Integrity time for sequential sequence on 32 KB block.	—	—	1024 x Tperiod x Nread	—
$t_{ai64kseq}$	Array Integrity time for sequential sequence on 64 KB block.	—	—	2048 x Tperiod x Nread	—

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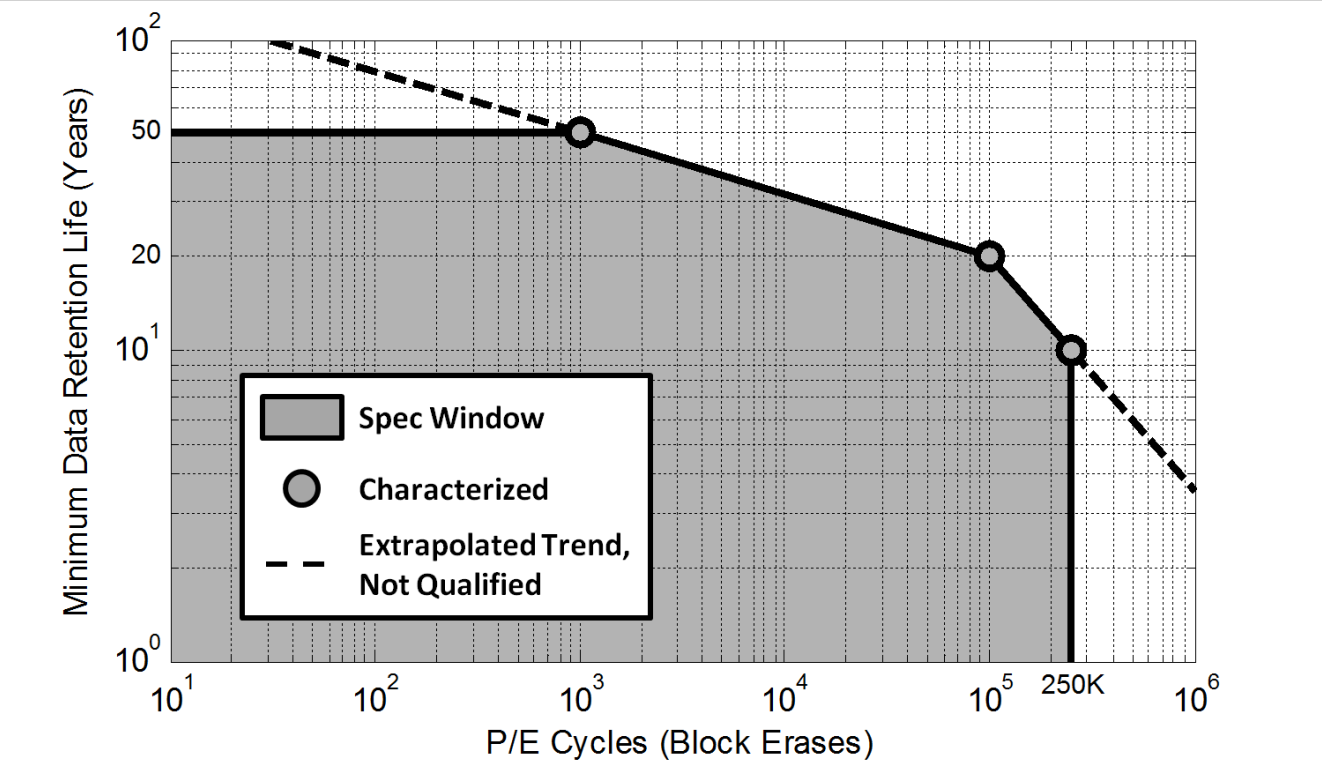


6.3.5 Flash memory AC timing specifications

Table 33. Flash memory AC timing specifications

Symbol	Characteristic	Min	Typical	Max	Units
t_{psus}	Time from setting the MCR-PSUS bit until MCR-DONE bit is set to a 1.	—	9.4 plus four system clock periods	11.5 plus four system clock periods	µs
t_{esus}	Time from setting the MCR-ESUS bit until MCR-DONE bit is set to a 1.	—	16 plus four system clock periods	20.8 plus four system clock periods	µs
t_{res}	Time from clearing the MCR-ESUS or PSUS bit with EHV = 1 until DONE goes low.	—	—	100	ns
t_{done}	Time from 0 to 1 transition on the MCR-EHV bit initiating a program/erase until the MCR-DONE bit is cleared.	—	—	5	ns
t_{dones}	Time from 1 to 0 transition on the MCR-EHV bit aborting a program/erase until the MCR-DONE bit is set to a 1.	—	16 plus four system clock periods	20.8 plus four system clock periods	µs

Table continues on the next page...

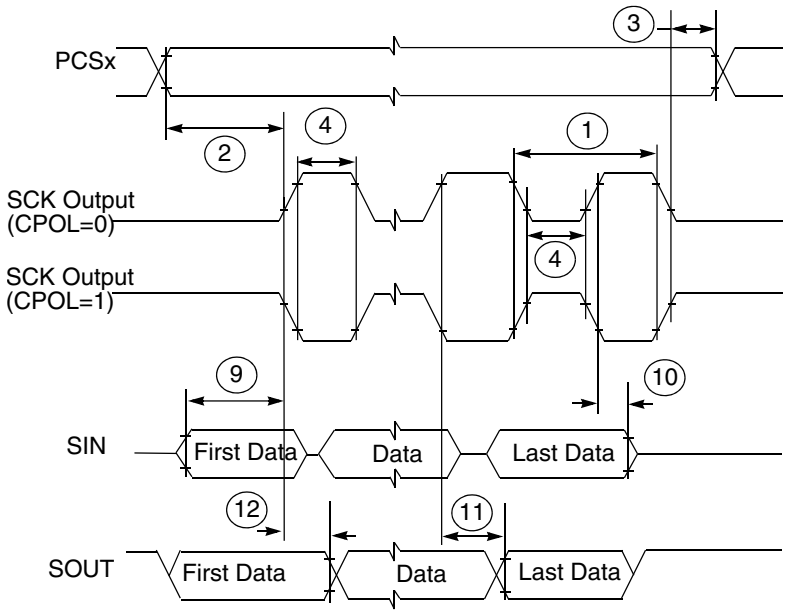


Figure 12. DSPI modified transfer format timing — master, CPHA = 0

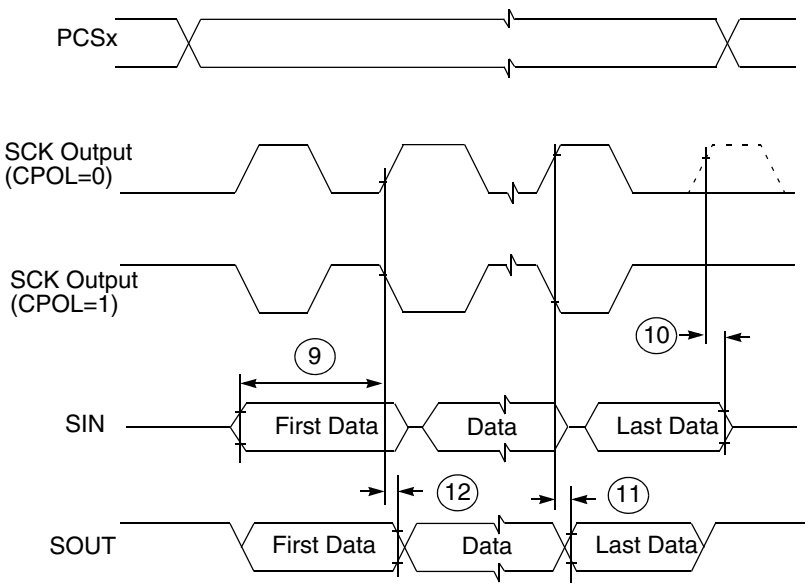
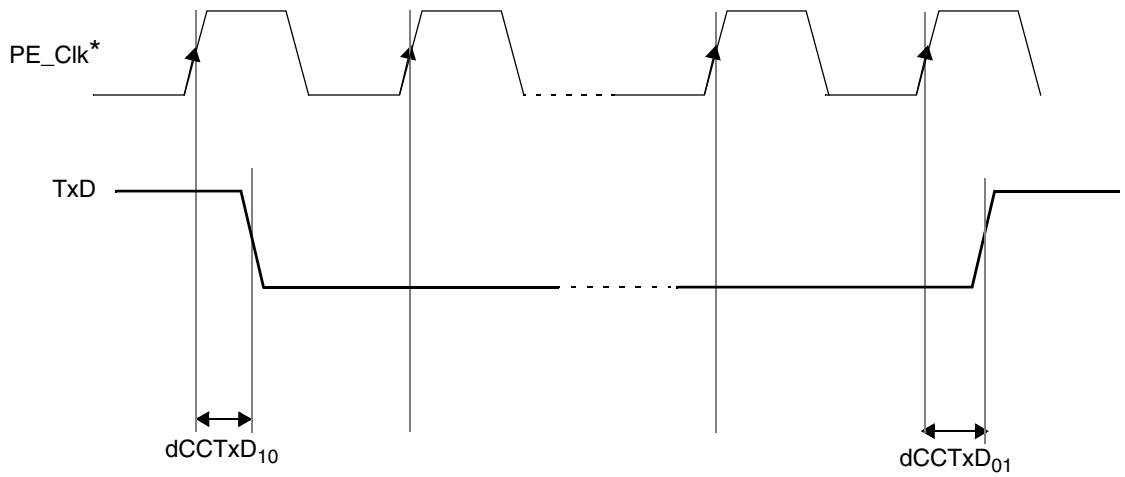


Figure 13. DSPI modified transfer format timing — master, CPHA = 1

Table 39. TxD output characteristics (continued)

Name	Description[1]	Min	Max	Unit
$dCCTxD_{01}$	Sum of delay between Clk to Q of the last FF and the final output buffer, rising edge	—	25	ns
$dCCTxD_{10}$	Sum of delay between Clk to Q of the last FF and the final output buffer, falling edge	—	25	ns

1. All parameters specified for $V_{DD\_HV\_IOx}$ = 3.3 V -5%, +±10%, TJ = –40 °C / 150 °C, TxD pin load maximum 25 pF.
2. For 3.3 V ± 10% operation, this specification is 10 ns.



*FlexRay Protocol Engine Clock

Figure 20. TxD Signal propagation delays

6.4.2.4 RxD

Table 40. RxD input characteristic

Name	Description[1]	Min	Max	Unit
C_CCRxD	Input capacitance on RxD pin	—	7	pF
uCCLogic_1	Threshold for detecting logic high	35	70	%
uCCLogic_0	Threshold for detecting logic low	30	65	%
$dCCRxD_{01}$	Sum of delay from actual input to the D input of the first FF, rising edge	—	10	ns
$dCCRxD_{10}$	Sum of delay from actual input to the D input of the first FF, falling edge	—	10	ns

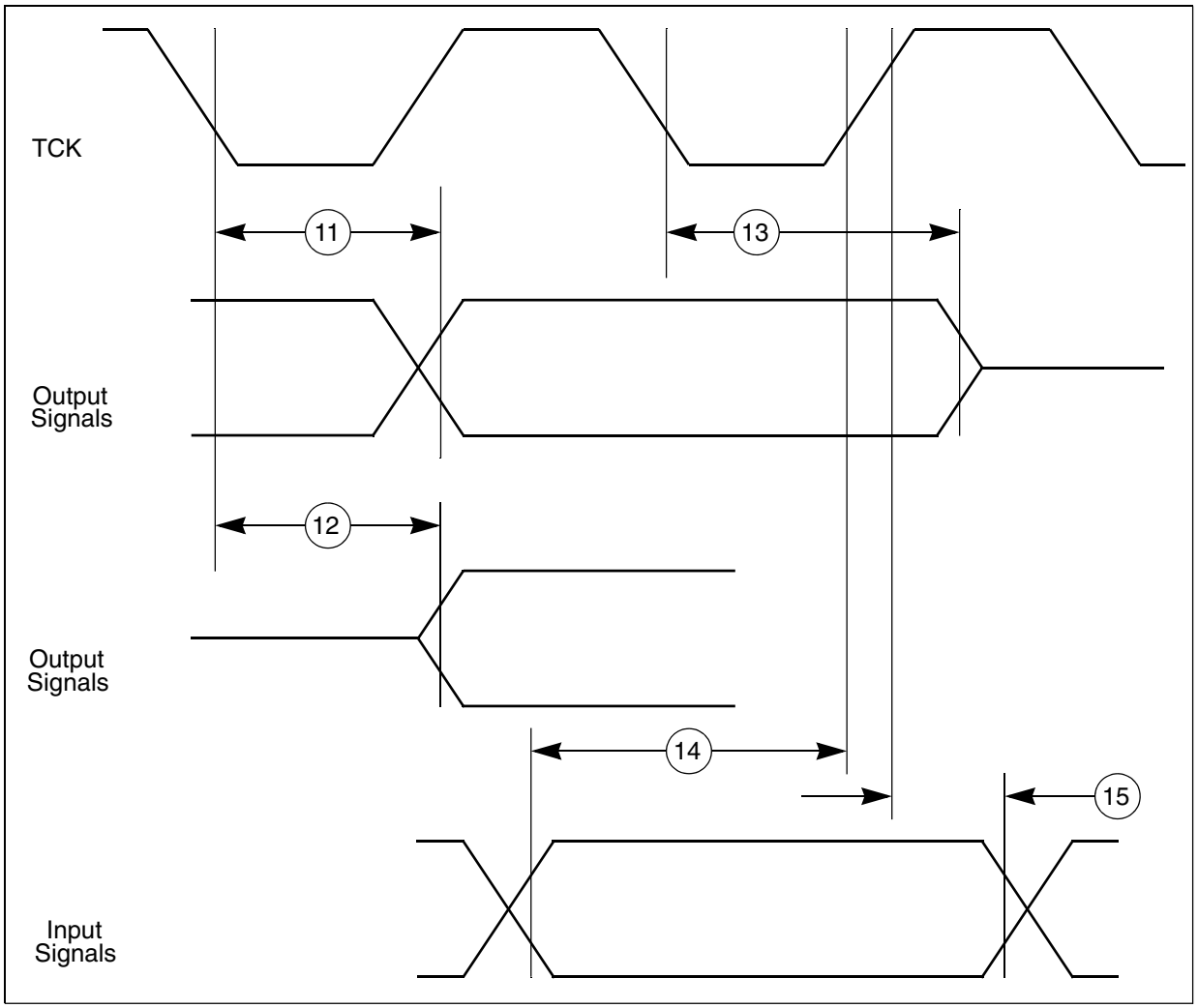


Figure 27. JTAG boundary scan timing

6.5.2 Nexus timing

Table 46. Nexus debug port timing [1]

No.	Symbol	Parameter	Conditions	Min	Max	Unit
1	t_{MCYC}	MCKO Cycle Time	—	15.6	—	ns
2	t_{MDC}	MCKO Duty Cycle	—	40	60	%
3	t_{MDOV}	MCKO Low to MDO, $\overline{\text{MSEO}}$, $\overline{\text{EVTO}}$ Data Valid[2]	—	–0.1	0.25	tMCYC
4	t_{EVTIPW}	$\overline{\text{EVTI}}$ Pulse Width	—	4	—	tTCYC
5	t_{EVTOPW}	$\overline{\text{EVTO}}$ Pulse Width	—	1	—	tMCYC
6	t_{TCYC}	TCK Cycle Time[3]	—	62.5	—	ns
7	t_{TDC}	TCK Duty Cycle	—	40	60	%
8	t_{NTDIS}, t_{NTMSS}	TDI, TMS Data Setup Time	—	8	—	ns

Table continues on the next page...

Table 46. Nexus debug port timing [1] (continued)

No.	Symbol	Parameter	Conditions	Min	Max	Unit
9	t_{NTDIH}, t_{NTMSH}	TDI, TMS Data Hold Time	—	5	—	ns
10	t_{JOV}	TCK Low to TDO/RDY Data Valid	—	0	25	ns

1. JTAG specifications in this table apply when used for debug functionality. All Nexus timing relative to MCKO is measured from 50% of MCKO and 50% of the respective signal.
2. For all Nexus modes except DDR mode, MDO, $\overline{\text{MSEO}}$, and $\overline{\text{EVTO}}$ data is held valid until next MCKO low cycle.
3. The system clock frequency needs to be four times faster than the TCK frequency.

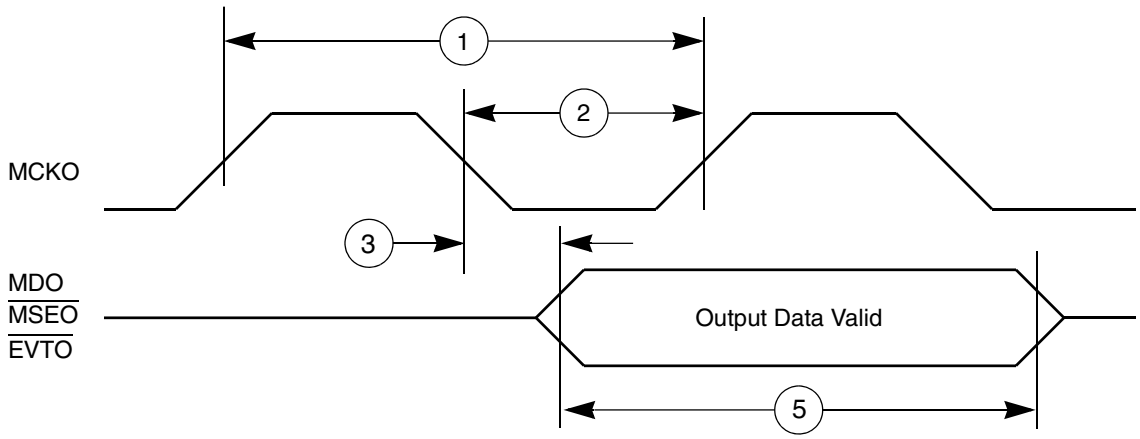


Figure 28. Nexus output timing

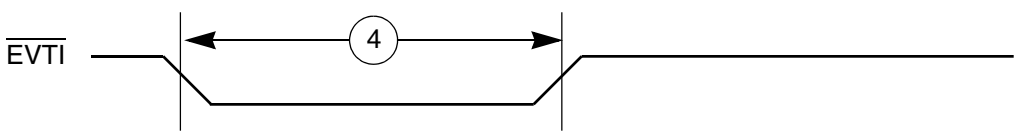


Figure 29. Nexus EVTI Input Pulse Width

Board type	Symbol	Description	324 MAPBGA	Unit	Notes
—	$R_{\theta JB}$	Thermal resistance, junction to board	16.8	°C/W	44
—	$R_{\theta JC}$	Thermal resistance, junction to case	7.4	°C/W	55
—	Ψ_{JT}	Thermal characterization parameter, junction to package top natural convection	0.2	°C/W	66
—	Ψ_{JB}	Thermal characterization parameter, junction to package bottom natural convection	7.3	°C/W	77

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
3. Per JEDEC JESD51-6 with the board horizontal
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.
7. Thermal characterization parameter indicating the temperature difference between package bottom center and the junction temperature per JEDEC JESD51-12. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.

Board type	Symbol	Description	256 MAPBGA	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	42.6	°C/W	11, 22
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	26.0	°C/W	1,2,33
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	31.0	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	21.3	°C/W	1,3
—	$R_{\theta JB}$	Thermal resistance, junction to board	12.8	°C/W	44

Table continues on the next page...

Board type	Symbol	Description	100 MAPBGA	Unit	Notes
—	$R_{\theta JB}$	Thermal resistance, junction to board	10.8	°C/W	44
—	$R_{\theta JC}$	Thermal resistance, junction to case	8.2	°C/W	55
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	0.2	°C/W	66
—	Ψ_{JB}	Thermal characterization parameter, junction to package bottom outside center (natural convection)	7.8	°C/W	77

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.
7. Thermal characterization parameter indicating the temperature difference between package bottom center and the junction temperature per JEDEC JESD51-12. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.

8 Dimensions

8.1 Obtaining package dimensions

Package dimensions are provided in package drawing.

To find a package drawing, go to www.nxp.com and perform a keyword search for the drawing's document number:

Package	NXP Document Number
100 MAPBGA	98ASA00802D

Table continues on the next page...

Package	NXP Document Number
176-pin LQFP-EP	98ASA00698D
256 MAPBGA	98ASA00346D
324 MAPBGA	98ASA10582D

9 Pinouts

9.1 Package pinouts and signal descriptions

For package pinouts and signal descriptions, refer to the Reference Manual.

10 Reset sequence

10.1 Reset sequence

This section describes different reset sequences and details the duration for which the device remains in reset condition in each of those conditions.

10.1.1 Reset sequence duration

Table 49 specifies the reset sequence duration for the five different reset sequences described in Reset sequence description.

Table 49. RESET sequences

No.	Symbol	Parameter	T_{Reset}			Unit
			Min	Typ [1, 1]	Max	
1	T_{DRB}	Destructive Reset Sequence, BIST enabled	6.2	7.3	-	ms
2	T_{DR}	Destructive Reset Sequence, BIST disabled	110	182	-	us
3	T_{ERLB}	External Reset Sequence Long, Unsecure Boot	6.2	7.3	-	ms
4	T_{FRL}	Functional Reset Sequence Long, Unsecure Boot	110	182	-	us
5	T_{FRS}	Functional Reset Sequence Short, Unsecure Boot	7	9	-	us

1. The Typ value is applicable only if the reset sequence duration is not prolonged by an extended assertion of RESET_B by an external reset generator.

10.1.2 BAF execution duration

Following table specifies the typical BAF execution time in case BAF boot header is present at first location (Typical) and last location (worst case). Total Boot time is the sum of reset sequence duration and BAF execution time.

Table 50. BAF execution duration

BAF execution duration	Min	Typ	Max	Unit
BAF execution time (boot header at first location)	—	200	—	µs
BAF execution time (boot header at last location)	—	—	320	µs

10.1.3 Reset sequence description

The figures in this section show the internal states of the device during the five different reset sequences. The dotted lines in the figures indicate the starting point and the end point for which the duration is specified in .

With the beginning of DRUN mode, the first instruction is fetched and executed. At this point, application execution starts and the internal reset sequence is finished.

The following figures show the internal states of the device during the execution of the reset sequence and the possible states of the RESET_B signal pin.

NOTE

RESET_B is a bidirectional pin. The voltage level on this pin can either be driven low by an external reset generator or by the device internal reset circuitry. A high level on this pin can only be generated by an external pullup resistor which is strong enough to overdrive the weak internal pulldown resistor. The rising edge on RESET_B in the following figures indicates the time when the device stops driving it low. The reset sequence durations given in are applicable only if the internal reset sequence is not prolonged by an external reset generator keeping RESET_B asserted low beyond the last Phase3.

Table 51. Revision History (continued)

Rev. No.	Date	Substantial Changes

		• In section: Voltage monitor electrical characteristics
		  • Updated description for Low Voltage detector block.
		  • Added note, BCP56, MCP68 and MJD31 are guaranteed ballasts.
		  • In table: Voltage regulator electrical specifications
		  • Added footnote, Ceramic X7R or X5R type with capacitance-temperature characteristics +/-15% of -55 degC to +125degC is recommended. The tolerance +/-20% is acceptable.
		  • Revised table, Voltage monitor electrical characteristics

		• In section: Supply current characteristics
		  • In table: Current consumption characteristics
		  • $I_{DD\_BODY\_4}$: Updated SYS_CLK to 120 MHz.
		  • $I_{DD\_BODY\_4}$: Updated Max for T_a= 105 °C fand 85 °C)
		  • I_{dd_STOP}: Added condition for T_a= 105 °C and removed Max value for T_a= 85 °C.
		  • $I_{DD\_HV\_ADC\_REF}$: Added condition for T_a= 105 °C and 85 °C and removed Max value for T_a= 25 °C.
		  • $I_{DD\_HV\_FLASH}$: Added condition for T_a= 105 °C and 85 °C
		  • In table: Low Power Unit (LPU) Current consumption characteristics
		  • LPU_RUN and LPU_STOP: Added condition for T_a= 105 °C and 85 °C
		  • In table: STANDBY Current consumption characteristics
		  • Added condition for T_a= 105 °C and 85 °C for all entries.
		
		• In section: I/O parameters
		  • In table: Functional Pad AC Specifications @ 3.3 V Range
		  • Updated values for 'pad_sr_hv (output)'
		  • In table: DC electrical specifications @ 3.3V Range
		  • Updateded Min and Max values for Vih and Vil respectively.
		  • In table: Functional Pad AC Specifications @ 5 V Range
		  • Updated values for 'pad_sr_hv (output)'
		  • In table DC electrical specifications @ 5 V Range
		  • Updated Min value for Vhys

Table continues on the next page...